

Substitute for form 1443/PTO		<b>Complete if Known</b>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (Use as many sheets as necessary)		Application Number	10/563.105-Conf. #4561
		Filing Date	December 30, 2005
		First Named Inventor	Misao TAKAKUSAKI
		Art Unit	1792
		Examiner Name	M. J. Song
Sheet	1	of	1
		Attorney Docket Number	1592-0159PUS1

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No.	Document Number Number/Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document Country Code <sup>2</sup> /Number/Kind Code <sup>3</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>4</sup>

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
	CA	MI et al., "Improvement of optical and electronic properties in broken gap mid-wave infrared laser materials," Conference on Lasers and Electro-Optics (CLEO 2001), Technical Digest, Postconference Edition, Baltimore, Md., May 6-11, 2001 (Trends in Optics and Photonics, (Tops)), US Washington, WA: OSA, US, Vol. 56, pp. 486-487, XP010560097	
	CB	HARPER et al., "Cross-sectional scanning tunneling microscopy characterization of molecular beam epitaxy grown InAs/GaSb/AlSb heterostructures for mid-infrared interband cascade lasers," Journal of Vacuum Science & Technology B: Microelectronicsprocessing and Phenomena, American Vacuum Society, New York, NY, US, Vol. 16, No. 3, May 1, 1998, pp. 1389-1394, XP012006832	
	CC	HASENBERG et al., "Molecular beam epitaxy growth and characterization of broken-gap (type II) superlattices and quantum wells for midwave-infrared laser diodes," Journal of Vacuum Science & Technology B: Microelectronicsprocessing and Phenomena, American Vacuum Society, New York, NY, US, Vol. 18, No. 3, May 1, 2000, pp. 1623-1627, XP012008258	
	CD	DESALVO et al., "Citric Acid Etching of GaAs <sub>1-x</sub> Sb <sub>x</sub> , Al <sub>0.5</sub> Ga <sub>0.5</sub> Sb, and InAs for Heterostructure Device Fabrication," Journal of the Electrochemical Society, Electrochemical Society, Manchester, New Hampshire, US, Vol. 141, No. 12, December 1, 1994, pp. 2526-2531, XP000495786	

Examiner Signature	Date Considered
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\*EXAMINER: initial if reference considered, whether or not citation is in conformance with MPEP 608. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. <sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> See Kinds, Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov) or MPEP 901.04. <sup>3</sup> Enter Office that issued the document, by the one-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language translation is attached.